

# IGBT Module

#### SK20GH065

**Preliminary Data** 

#### **Features**

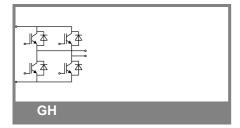
- · Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N-channel homogeneous Silicon structure (NPT-NonPunchThrough IGBT)
- High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no E63532

### Typical Applications\*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

Absolute Maximum Ratings T <sub>s</sub> = 25 °C, unless otherwise specified								
Symbol	Conditions		Values	Units				
IGBT				_				
$V_{CES}$	T <sub>j</sub> = 25 °C		600	V				
I <sub>C</sub>	T <sub>j</sub> = 125 °C	T <sub>s</sub> = 25 °C	24	Α				
		T <sub>s</sub> = 80 °C	18	Α				
I <sub>CRM</sub>	I <sub>CRM</sub> = 2 x I <sub>Cnom</sub>		40	Α				
$V_{GES}$			± 20	V				
t <sub>psc</sub>	$V_{CC}$ = 300 V; $V_{GE} \le$ 20 V; VCES < 600 V	T <sub>j</sub> = 125 °C	10	μs				
Inverse Diode								
I <sub>F</sub>	T <sub>j</sub> = 125 °C	$T_s = 25 ^{\circ}C$	25	Α				
		T <sub>s</sub> = 80 °C	18	Α				
I <sub>FRM</sub>	I <sub>FRM</sub> = 2 x I <sub>Fnom</sub>		40	Α				
Module								
I <sub>t(RMS)</sub>				Α				
$T_{vj}$			-40 <b>+</b> 150	°C				
T <sub>stg</sub>			-40 <b>+</b> 125	°C				
V <sub>isol</sub>	AC, 1 min.		2500	V				

Characteristics $T_s =$			25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
$V_{\text{GE(th)}}$	$V_{GE} = V_{CE}$ , $I_{C} = 0.5$ mA		3	4	5	V	
I <sub>CES</sub>	$V_{GE} = 0 V, V_{CE} = V_{CES}$	T <sub>j</sub> = 25 °C			0,07	mA	
$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}$	T <sub>j</sub> = 25 °C			120	nA	
$V_{CE0}$		T <sub>j</sub> = 25 °C		1		V	
		T <sub>j</sub> = 125 °C		1,1		V	
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C				mΩ	
		T <sub>j</sub> = 125°C		55		mΩ	
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 20 A, V <sub>GE</sub> = 15 V			2		V	
		$T_j = 125^{\circ}C_{chiplev.}$		2,2		V	
C <sub>ies</sub>				1,1		nF	
C <sub>oes</sub>	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,107		nF	
C <sub>res</sub>				0,063		nF	
t <sub>d(on)</sub>				21		ns	
t <sub>r</sub>	$R_{Gon} = 30 \Omega$	V <sub>CC</sub> = 300V		28		ns	
E <sub>on</sub>		I <sub>C</sub> = 20A		0,6		mJ	
t <sub>d(off)</sub>	$R_{Goff} = 30 \Omega$	T <sub>j</sub> = 125 °C		170		ns	
t <sub>f</sub>		V <sub>GE</sub> =±15V		20		ns	
$E_{off}$				0,4		mJ	
$R_{th(j-s)}$	per IGBT				1,7	K/W	





SEMITOP<sup>®</sup> 2

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Characteristics									
Symbol	Conditions		min.	typ.	max.	Units			
Inverse Diode									
$V_F = V_{EC}$	$I_{Fnom}$ = 20 A; $V_{GE}$ = 0 V	$T_j = 25  ^{\circ}C_{\text{chiplev.}}$		1,6		V			
		$T_j = 125  ^{\circ}C_{chiplev.}$		1,6		V			
$V_{F0}$		T <sub>j</sub> = 25 °C				V			
		T <sub>j</sub> = 125 °C		0,9		V			
r <sub>F</sub>		T <sub>j</sub> = 25 °C		30		mΩ			
		T <sub>j</sub> = 125 °C		33		$m\Omega$			
I <sub>RRM</sub>	I <sub>F</sub> = A	T <sub>i</sub> = 125 °C				Α			
$Q_{rr}$		•				μC			
E <sub>rr</sub>	V <sub>R</sub> = 300V					mJ			
R <sub>th(j-s)D</sub>	per diode				1,7	K/W			
$M_s$	to heat sink				2	Nm			
w				19		g			

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

